

# Silicon Diode

## **BYVF32-100**

Fast Efficient Rectifier

100V / 18A

# DATASHEET

from

[www.web-bcs.com](http://www.web-bcs.com)

OEM – General Semiconductor

Source: General Semiconductor Databook 1998

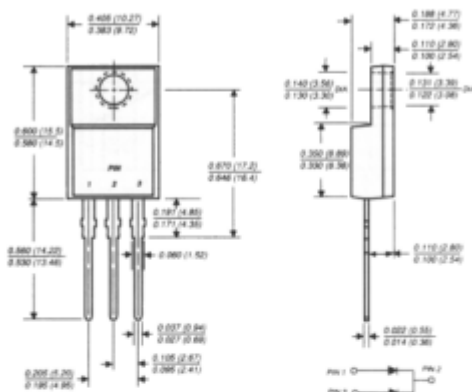
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# BYVF32-50 THRU BYVF32-200

## FAST EFFICIENT PLASTIC RECTIFIER

Reverse Voltage - 50 to 150 Volts Forward Current - 18.0 Amperes

### ITO-220AB



Dimensions in inches and (millimeters)

### FEATURES

- Dual rectifier construction, positive centertap
- Plastic package has Underwriters Laboratory Flammability Classification 94V-0
- Glass passivated chip junctions
- Low power loss
- Low forward voltage, high current capability
- High surge capability
- Superfast recovery time for high efficiency
- High temperature soldering guaranteed: 250°C, 0.25" (6.35mm) from case for 10 seconds

### MECHANICAL DATA

**Case:** JEDEC ITO-220AB molded plastic body  
**Terminals:** Plated leads solderable per MIL-STD-750, Method 2026  
**Polarity:** As marked  
**Mounting Position:** Any  
**Weight:** 0.08 ounce, 2.24 grams  
**Mounting Torque:** 5in -lbs. max.

### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

	SYMBOLS	BYVF32-50	BYVF32-100	BYVF32-150	BYVF32-200	UNITS
Maximum repetitive peak reverse voltage	VRRM	50	100	150	200	Volts
Maximum RMS voltage	VRMS	35	70	105	140	Volts
Maximum DC blocking voltage	VDC	50	100	150	200	Volts
Maximum average forward rectified current at TC=120°C	IAV	18.0				Amps
Peak forward surge current 10ms single half sine-wave superimposed at at TJ=150°C	IFSM	150.0				Amps
Maximum instantaneous forward voltage per leg at: IF=20A, IF=5.0A, TJ=100°C	VF	1.15 0.85				Volts
Maximum DC reverse current at rated DC blocking voltage TC=25°C TC=100°C	IR	10.0 600.0				µA
Maximum reverse recovery time per leg (NOTE 1)	trr	25.0				ns
Typical junction capacitance (NOTE 2)	CJ	45.0				pF
Maximum thermal resistance per leg (NOTE 3)	REJC	5.0				°C/W
Operating and storage temperature range	TJ, TSTG	-65 to +150				°C

**NOTES:**

- (1) Reverse recovery test conditions: IF=1A VR=30V, di/dt=100A/µs, Irr=10% Irsm
- (2) Measured at 1.0 MHz and applied reverse voltage of 4.0 Volts
- (3) Thermal resistance from junction to ambient and from junction to case per leg mounted on heatsink

**RATINGS AND CHARACTERISTIC CURVES BYVF32-50 THRU BYVF32-200**

